TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

HN1A01FU

Audio Frequency General Purpose Amplifier Applications

Unit: mm

- Small package (Dual type) •
- High voltage and high current •

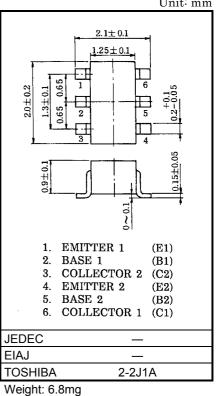
 $: V_{CEO} = -50V, I_{C} = -150mA (max)$

- High h_{FE} : $h_{FE} = 120 \sim 400$ •
- Excellent hFE linearity •

 h_{FE} (IC =-0.1mA) / h_{FE} (IC =-2mA) = 0.95 (typ.)

Maximum Ratings (Ta = 25°C) (Q1, Q2 Common)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	-50	V
Collector-emitter voltage	V _{CEO}	-50	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	Ι _C	-150	mA
Base current	Ι _Β	-30	mA
Collector power dissipation	P _C *	200	mW
Junction temperature	Tj	125	°C
Storage temperature range	T _{stg}	-55~125	°C



* Total rating

Electrical Characteristics (Ta = 25°C) (Q1,Q2 Common)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	_	$V_{CB} = -50V, I_E = 0$	_	_	-0.1	μA
Emitter cut-off current	I _{EBO}	—	$V_{EB} = -5V, I_{C} = 0$	_	_	-0.1	μA
DC current gain	h _{FE (Note)}	—	$V_{CE} = -6V$, $I_C = -2mA$	120	_	400	
Collector-emitter saturation voltage	V _{CE (sat)}	_	I _C = -100mA, I _B = -10mA	_	-0.1	-0.3	V
Transition frequency	f _T	—	$V_{CE} = -10V, I_C = -1mA$	80	_	_	MHz
Collector output capacitance	C _{ob}	-	V_{CB} = -10V, I _E = 0, f = 1MHz		4	7	pF

Note: hFE Classification

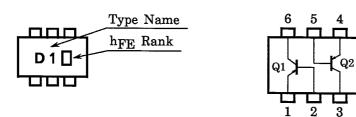
Y (Y): 120~240, GR (G): 200~400

() Marking Symbol



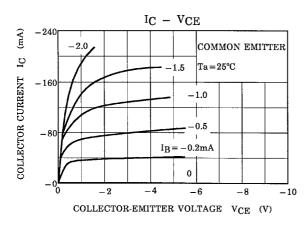
Marking

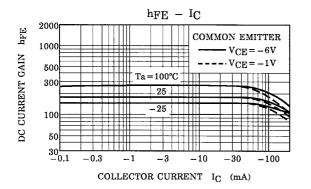
Equivalent Circuit (Top View)

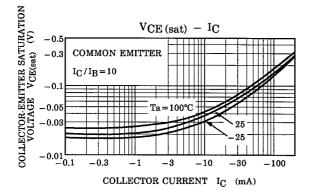


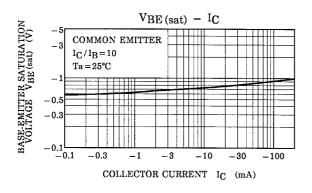
TOSHIBA

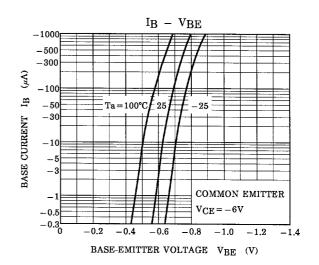
(Q1,Q2 Common)

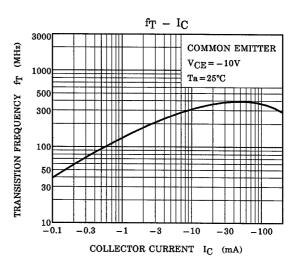


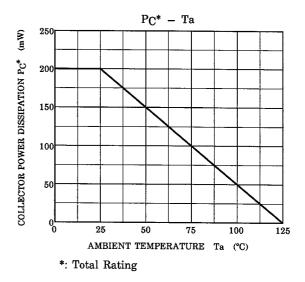












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